

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Patent No. .... 7037862B2  
Patent Issue Date ..... May 2, 2006  
Application Serial No. .... 09881408  
Filing Date ..... June 13, 2001  
Assignee ..... Micron Technology, Inc.  
Inventorship ..... Ahn, Kie Y.  
Attorney's Docket No. .... MI22-1534  
Title: ..... A Dielectric Layer Forming Method and Devices Formed Therewith

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT  
FOR APPLICANT MISTAKES AND PTO MISTAKES (37 C.F.R. 1.322(a) and  
1.323)**

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450  
ATTN: Decision and Certificate of Correction  
Branch of the Patent Issue Division

From: James E. Lake (Tel. 509-624-4276; Fax 509-838-3424)  
Wells St. John P.S.  
601 W. First Avenue, Suite 1300  
Spokane, WA 99201-3828

Sir/Madam:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7037862B2, granted May 2, 2006, in accordance with the Certificate of Correction form attached hereto.

It is noted that errors appear in this patent of a typographical nature of character, as more fully described below. The error(s) occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination.

The exact page and line number where the error occurs in the application file are:

**Pg. 4, line 8 in the specification/Col. 2, line 24 in the issued patent;**  
**Pg. 13, ¶ [0027], line 4 in the specification/Col. 5, line 37 in the issued patent;**  
**Pg. 15, ¶ [0029], line 3 in the specification/Col. 6, line 7 in the issued patent;**  
**Pg. 19, line 15 in the specification/Col. 7, line 67 in the issued patent;**  
**Pg. 22, ¶ [0040], line 10 in the specification/Col. 9, line 13 in the issued patent; and**  
**Pg. 25, claim 11, line 2 in the specification/Col. 9, line 61, claim 8 in issued patent.**

Also enclosed is a copy of form PTO-892 from the June 27, 2003 Office Action and the July 7, 2003 facsimile sent to the Applicant by the Examiner correcting a patent number cited by the Examiner in PTO-892.


The other error(s) listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto is Form PTO-1050 which is suitable for printing.

The Director is hereby authorized to charge the \$100.00 fee as required under 37 CFR § 1.20(a) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 04 Mar 2008

By:   
James E. Lake  
Reg. No. 44854

<b>Notice of References Cited</b>	Application/Control No 09/881,408	Applicant(s)/Patent Under Reexamination AHN ET AL.	
	Examiner Thao X Le	Art Unit 2814	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0047170	04-2002	Ota, Kazunobu	257/410
*	B	US-6,184,072	02-2001	Kaushik et al.	438/197
	C	US-601,353	03-1898	Name not available	440/34
✓	D	US-6,395,650	05-2002	Callegari et al.	438/785
✓	E	US-6,444,592	09-2002	Ballantine et al.	438/770
✓	F	US-6,297,539	10-2001	Ma et al.	257/410
✓	G	US-6,476,454	11-2002	Suguro, Kyoichi	257/410
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

USPTO  
Washington, D.C. 20231

USPTO

# Fax

COPY

M22-1534

<b>To:</b> Mr. James Lake	<b>From:</b> Thao Le
<b>Fax:</b> 509-838-3424	<b>Pages:</b> 11
<b>Phone:</b>	<b>Date:</b> 7/2/03
<b>Re:</b> Application Serial#09/881408	<b>CC:</b>

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• **Comments:**

Attached please find the reference 6013553.

Sorry about the typographical errors.

Regards,

T. Le

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CERTIFICATE OF CORRECTION

Page 1 of 3

PATENT NO. : 7037862B2  
APPLICATION NO.: 09881408  
DATED : May 2, 2006  
INVENTOR(S) : Ahn, Kie Y.; Forbes, Leonard

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Pg. 2, col.1, U.S. PATENT DOCUMENTS –

Please insert the following patents:

--6,013,553	*	1/2000	Wallace et al.
6,348,373	*	2/2002	Ma et al.
6,407,435		6/2002	Ma et al.
6,495,474		12/2002	Rafferty et al.
6,573,160		6/2003	Taylor et al.
6,632,729	*	10/2003	Paton
6,679,996	*	1/2004	Yao
6,713,846		3/2004	Senzaki
6,784,508	*	8/2004	Tsunashima et al.
2002/0190302		12/2002	Bojarczuk et al.--

Col. 2, line 24 –

Replace “additional requirements. Thus it would desirable provide”  
With --additional requirements. Thus it would be desirable to provide--

Col. 5, line 37 –

Replace “evaporative processes and in particular an electron beam”  
With --evaporative process and in particular an electron beam--

Col. 6, line 7 –

Replace “by using a physical deposition (PVD) method as previously”  
With --by using a physical vapor deposition (PVD) method as previously--

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UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

Page 2 of 3

PATENT NO. : 7037862B2

APPLICATION NO.: 09881408

DATED : May 2, 2006

INVENTOR(S) : Ahn, Kie Y.; Forbes, Leonard

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 7, line 67 –

Replace “oxidation conditions only one effective method and that”

With --oxidation conditions represent only one effective method and that--

Col. 9, line 13 –

Replace “will be understood that the selection of Hf and La form the”

With --will be understood that the selection of Hf and La to form the--

Col. 9, line 36, claim 1-

Replace “the second layer to temperature effective to form a first”

With --the second layer to a temperature effective to form a first--

Col. 9, line 61, claim 8 –

Replace “heating to a temperature from about 200° C. to about 400 C.”

With --heating to a temperature from about 200° C. to about 400° C.--

Col. 10, line 42, claim 17 –

Replace “heating the metal lever and layer of silicon dioxide to a”

With --heating the metal layer and layer of silicon dioxide to a--

Col. 10, line 47, claim 17 –

Replace “dielectric lever over the surface, all the metal of the first”

With --dielectric layer over the surface, all the metal of the first--

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Page 3 of 3

PATENT NO. : 7037862B2

APPLICATION NO.: 09881408

DATED : May 2, 2006

INVENTOR(S) : Ahn, Kie Y.; Forbes, Leonard

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 11, line 17, claim **22** –

Replace “heating to a temperature from about 200° C. to about 200°”

With --heating to a temperature from about 200° C. to about 400°--

Col. 12, lines 15-16, claim **23** –

Replace “the raction chamber and heating the hafnium-containing”

With --the reaction chamber and heating the hafnium-containing--

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